

Jian-Dong Ye

List of Publications by Year in descending order

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120
papers

3,629
citations

147801

31
h-index

161849

54
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123
all docs

123
docs citations

123
times ranked

2997
citing authors

#	ARTICLE	IF	CITATIONS
1	Review of gallium-oxide-based solar-blind ultraviolet photodetectors. <i>Photonics Research</i> , 2019, 7, 381.	7.0	391
2	Electroluminescent and transport mechanisms of n-ZnO/p-Si heterojunctions. <i>Applied Physics Letters</i> , 2006, 88, 182112.	3.3	233
3	Solar-Blind Photodetector with High Avalanche Gains and Bias-Tunable Detecting Functionality Based on Metastable Phase β -Ga ₂ O ₃ /ZnO Isotype Heterostructures. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 36997-37005.	8.0	158
4	A 1.86-kV double-layered NiO/β-Ga ₂ O ₃ vertical p-n heterojunction diode. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	136
5	Carbonized Bamboos as Excellent 3D Solar Vapor Generation Devices. <i>Advanced Materials Technologies</i> , 2019, 4, 1800593.	5.8	107
6	Demonstration of the p-NiO _x /n-Ga ₂ O ₃ Heterojunction Gate FETs and Diodes With BV ² /Ron,sp Figures of Merit of 0.39 GW/cm ² and 1.38 GW/cm ² . <i>IEEE Electron Device Letters</i> , 2021, 42, 485-488.	3.9	86
7	Split Bullseye Shaped Aluminum Antenna for Plasmon-Enhanced Nanometer Scale Germanium Photodetector. <i>Nano Letters</i> , 2011, 11, 1289-1293.	9.1	80
8	1.37 kV/12 A NiO/β-Ga ₂ O ₃ Heterojunction Diode With Nanosecond Reverse Recovery and Rugged Surge-Current Capability. <i>IEEE Transactions on Power Electronics</i> , 2021, 36, 12213-12217.	7.9	77
9	Gallium oxide-based solar-blind ultraviolet photodetectors. <i>Semiconductor Science and Technology</i> , 2020, 35, 023001.	2.0	73
10	β-Ga ₂ O ₃ hetero-junction barrier Schottky diode with reverse leakage current modulation and BV ² /Ron,sp value of 0.93 GW/cm ² . <i>Applied Physics Letters</i> , 2021, 118, .	3.3	72
11	2.41 kV Vertical P-NiO/n-Ga ₂ O ₃ Heterojunction Diodes With a Record Baliga's Figure-of-Merit of 5.18 GW/cm ² . <i>IEEE Transactions on Power Electronics</i> , 2022, 37, 3743-3746.	7.9	72
12	β-Ga ₂ O ₃ vertical heterojunction barrier Schottky diodes terminated with p-NiO field limiting rings. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	65
13	Two-dimensional electron gas in Zn-polar ZnMgO/ZnO heterostructure grown by metal-organic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2010, 97, .	3.3	64
14	Band Alignment and Interface Recombination in NiO/β-Ga ₂ O ₃ Type-II p-n Heterojunctions. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 3341-3347.	3.0	63
15	1.95-kV Beveled-Mesa NiO/β-Ga ₂ O ₃ Heterojunction Diode With 98.5% Conversion Efficiency and Over Million-Times Overvoltage Ruggedness. <i>IEEE Transactions on Power Electronics</i> , 2022, 37, 1223-1227.	7.9	60
16	Carrier Transport and Gain Mechanisms in Ga ₂ O ₃ -Based Metal-Semiconductor-Metal Solar-Blind Schottky Photodetectors. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2276-2281.	3.0	59
17	Deep-level defects in gallium oxide. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 043002.	2.8	57
18	Toward emerging gallium oxide semiconductors: A roadmap. <i>Fundamental Research</i> , 2021, 1, 697-716.	3.3	56

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19	Highly Narrow-Band Polarization-Sensitive Solar-Blind Photodetectors Based on $\text{In}^{2+}\text{-Ga}_2\text{O}_3$ Single Crystals. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 7131-7137.	8.0	55
20	Origins of green band emission in high-temperature annealed N-doped ZnO. <i>Journal of Luminescence</i> , 2011, 131, 1189-1192.	3.1	51
21	Recent progress of the native defects and p-type doping of zinc oxide. <i>Chinese Physics B</i> , 2017, 26, 047702.	1.4	51
22	Raman-active Fröhlich optical phonon mode in arsenic implanted ZnO. <i>Applied Physics Letters</i> , 2009, 94, 011913.	3.3	49
23	Sustainable Solar Evaporation while Salt Accumulation. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 4935-4942.	8.0	46
24	Heteroepitaxial growth of thick $\text{In}^{2+}\text{-Ga}_2\text{O}_3$ film on sapphire (0001) by MIST-CVD technique. <i>Journal of Semiconductors</i> , 2019, 40, 012804.	3.7	45
25	Identification and modulation of electronic band structures of single-phase $\text{In}^{2+}\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$ alloys grown by laser molecular beam epitaxy. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	43
26	Localized surface plasmon enhanced Ga_2O_3 solar blind photodetectors. <i>Optics Express</i> , 2020, 28, 5731.	3.4	42
27	Low density of interface trap states and temperature dependence study of Ga_2O_3 Schottky barrier diode with p-NiOx termination. <i>Applied Physics Letters</i> , 2022, 120, .	3.3	38
28	On the origin of dislocation generation and annihilation in $\text{In}^{2+}\text{-Ga}_2\text{O}_3$ epilayers on sapphire. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	37
29	Tellurium assisted realization of p-type N-doped ZnO. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	36
30	Magnesium ion-implantation-based gallium nitride p-i-n photodiode for visible-blind ultraviolet detection. <i>Photonics Research</i> , 2019, 7, B48.	7.0	36
31	Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on III-Nitride Semiconductors. <i>Advanced Materials</i> , 2020, 32, e1904354.	21.0	34
32	Vertically Emitting Indium Phosphide Nanowire Lasers. <i>Nano Letters</i> , 2018, 18, 3414-3420.	9.1	33
33	Nanoplasmonically Enhanced High-Performance Metastable Phase $\text{In}^{2+}\text{-Ga}_2\text{O}_3$ Solar-Blind Photodetectors. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 40283-40289.	8.0	31
34	Carbonized Tree-Like Furry Magnolia Fruit-Based Evaporator Replicating the Feat of Plant Transpiration. <i>Global Challenges</i> , 2019, 3, 1900040.	3.6	30
35	Two-dimensional electron gas related emissions in ZnMgO/ZnO heterostructures. <i>Applied Physics Letters</i> , 2011, 99, .	3.3	27
36	Transition of photoconductive and photovoltaic operation modes in amorphous Ga_2O_3 -based solar-blind detectors tuned by oxygen vacancies. <i>Chinese Physics B</i> , 2019, 28, 028501.	1.4	26

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37	Band alignment and band bending at In^{\pm} -Ga ₂ O ₃ /ZnO n-n isotype hetero-interface. Applied Physics Letters, 2019, 115, .	3.3	25
38	Influence of thermally diffused aluminum atoms from sapphire substrate on the properties of ZnO epilayers grown by metal-organic chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2011, 29, .	2.1	24
39	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. Scientific Reports, 2019, 9, 8796.	3.3	24
40	In situ heteroepitaxial construction and transport properties of lattice-matched Ir_2O_3 -Ga ₂ O ₃ p-n heterojunction. Applied Physics Letters, 2021, 118, .	3.3	24
41	Over 1.8 GW/cm ² beveled-mesa NiO/ In^{\pm} -Ga ₂ O ₃ heterojunction diode with 800 V/10 A nanosecond switching capability. Applied Physics Letters, 2021, 119, .	3.3	24
42	Ellipsometric determination of anisotropic optical constants of single phase Ga ₂ O ₃ thin films in its orthorhombic and monoclinic phases. Optical Materials, 2020, 102, 109807.	3.6	23
43	Majority and Minority Carrier Traps in NiO/ In^{\pm} -Ga ₂ O ₃ p ⁺ -n Heterojunction Diode. IEEE Transactions on Electron Devices, 2022, 69, 981-987.	3.0	23
44	Fast Speed Ga ₂ O ₃ Solar-blind Schottky Photodiodes with Large Sensitive Area. IEEE Electron Device Letters, 2020, , 1-1.	3.9	22
45	Surfactant effect of arsenic doping on modification of ZnO (0001) growth kinetics. Applied Physics Letters, 2009, 95, 101905.	3.3	21
46	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. Scientific Reports, 2016, 6, 23486.	3.3	21
47	Effects of Post Annealing on Electrical Performance of Polycrystalline Ga ₂ O ₃ Photodetector on Sapphire. Nanoscale Research Letters, 2020, 15, 100.	5.7	21
48	Temperature-dependent photoluminescence of ZnO films codoped with tellurium and nitrogen. Journal of Applied Physics, 2012, 112, 103534.	2.5	20
49	Defect formation and thermal stability of H in high dose H implanted ZnO. Journal of Applied Physics, 2013, 114, 083111.	2.5	19
50	Identification of defect-related emissions in ZnO hybrid materials. Applied Physics Letters, 2015, 107, .	3.3	19
51	Zinc vacancy related emission in homoepitaxial N-doped ZnO microrods. Journal of Luminescence, 2015, 161, 293-299.	3.1	19
52	Highly efficient solar steam generation by hybrid plasmonic structured TiN/mesoporous anodized alumina membrane. Journal of Materials Research, 2018, 33, 3857-3869.	2.6	19
53	High- k HfO ₂ -Based AlGa ₂ N/GaN MIS-HEMTs With Y ₂ O ₃ Interfacial Layer for High Gate Controllability and Interface Quality. IEEE Journal of the Electron Devices Society, 2020, 8, 15-19.	2.1	19
54	70- μ m-Body Ga ₂ O ₃ Schottky Barrier Diode With 1.48 K/W Thermal Resistance, 59 A Surge Current and 98.9% Conversion Efficiency. IEEE Electron Device Letters, 2022, 43, 773-776.	3.9	19

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55	Anion Engineering Enhanced Response Speed and Tunable Spectral Responsivity in Gallium-Oxynitrides-Based Ultraviolet Photodetectors. <i>ACS Applied Electronic Materials</i> , 2020, 2, 808-816.	4.3	18
56	Structural transition, subgap states, and carrier transport in anion-engineered zinc oxynitride nanocrystalline films. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	17
57	Plasmon-enhanced photoelectrochemical water splitting by InGaN/GaN nano-photoanodes. <i>Semiconductor Science and Technology</i> , 2020, 35, 025017.	2.0	17
58	Spin-polarized Wide Electron Slabs in Functionally Graded Polar Oxide Heterostructures. <i>Scientific Reports</i> , 2012, 2, 533.	3.3	16
59	The suppression of zinc interstitial related shallow donors in Te-doped ZnO microrods. <i>Journal of Alloys and Compounds</i> , 2018, 735, 1232-1238.	5.5	16
60	Highly Enhanced Inductive Current Sustaining Capability and Avalanche Ruggedness in GaN p-i-n Diodes With Shallow Bevel Termination. <i>IEEE Electron Device Letters</i> , 2020, 41, 469-472.	3.9	16
61	Second-order surface-plasmon assisted responsivity enhancement in germanium nano-photodetectors with bullâ€™s eye antennas. <i>Optics Express</i> , 2014, 22, 15949.	3.4	15
62	A Terahertz Controlledâ€™NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials. <i>Advanced Optical Materials</i> , 2017, 5, 1700108.	7.3	15
63	Sulfur regulation of boron doping and growth behavior for high-quality diamond in microwave plasma chemical vapor deposition. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	15
64	Band Alignment and Enhanced Interfacial Conductivity Manipulated by Polarization in a Surfactant-Mediated Grown $\text{In}_{0.2}\text{Ga}_{0.8}\text{O}_{3.2}$ /In ₂ O ₃ Heterostructure. <i>ACS Applied Electronic Materials</i> , 2021, 3, 795-803.	4.3	15
65	Applications of AlGaIn/GaN high electron mobility transistor-based sensors in water quality monitoring. <i>Semiconductor Science and Technology</i> , 2020, 35, 123001.	2.0	15
66	Demonstration of $\text{In}_{0.2}\text{Ga}_{0.8}\text{O}_{3.2}$ Superjunction-Equivalent MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 2203-2209.	3.0	15
67	Spin-polarized two-dimensional electron gas in undoped $\text{Mg}_{1-x}\text{Zn}_x\text{O}/\text{ZnO}$ heterostructures. <i>Applied Physics Letters</i> , 2012, 100, 192105.	3.3	14
68	Nitrogen modulation of boron doping behavior for accessible n-type diamond. <i>APL Materials</i> , 2021, 9, .	5.1	14
69	A self-powered solar-blind photodetector based on polyaniline/ $\text{In}_{0.2}\text{Ga}_{0.8}\text{O}_{3.2}$ heterojunction. <i>Applied Physics Letters</i> , 2021, 119, .	3.3	14
70	High-Responsivity and Fast-Response Ultraviolet Phototransistors Based on Enhanced p-GaN/AlGaIn/GaN HEMTs. <i>ACS Photonics</i> , 2022, 9, 2040-2045.	6.6	14
71	Anisotropy and in-plane polarization of low-symmetrical $\text{In}_{0.2}\text{Ga}_{0.8}\text{O}_{3.2}$ single crystal in the deep ultraviolet band. <i>Applied Surface Science</i> , 2020, 527, 146648.	6.1	13
72	Enhanced Contactless Salt-Collecting Solar Desalination. <i>ACS Applied Materials & Interfaces</i> , 2022, 14, 34151-34158.	8.0	13

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73	Identification and control of native defects in N-doped ZnO microrods. <i>Optical Materials Express</i> , 2016, 6, 2847.	3.0	12
74	Extreme absorption enhancement in ZnTe:O/ZnO intermediate band core-shell nanowires by interplay of dielectric resonance and plasmonic bowtie nanoantennas. <i>Scientific Reports</i> , 2017, 7, 7503.	3.3	12
75	The effect of oxygen annealing on characteristics of In^{2-} -Ga $_{2}\text{O}_3$ solar-blind photodetectors on SiC substrate by ion-cutting process. <i>Journal of Alloys and Compounds</i> , 2021, 889, 161743.	5.5	12
76	Label-free fiber nanograting sensor for real-time in situ early monitoring of cellular apoptosis. <i>Advanced Photonics</i> , 2022, 4, .	11.8	12
77	Anomalous circular photogalvanic effect of the spin-polarized two-dimensional electron gas in Mg $_{0.2}$ Zn $_{0.8}$ O/ZnO heterostructures at room temperature. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	11
78	Annealing in tellurium-nitrogen co-doped ZnO films: The roles of intrinsic zinc defects. <i>Journal of Applied Physics</i> , 2015, 117, 135304.	2.5	11
79	The roles of buffer layer thickness on the properties of the ZnO epitaxial films. <i>Applied Surface Science</i> , 2016, 388, 557-564.	6.1	11
80	Formation of V Zn -N O acceptors with the assistance of tellurium in nitrogen-doped ZnO films. <i>Journal of Alloys and Compounds</i> , 2017, 699, 484-488.	5.5	11
81	M-Plane $\text{In-Ga}, \text{O}, \text{f}$ Solar-Blind Detector With Record-High Responsivity-Bandwidth Product and High-Temperature Operation Capability. <i>IEEE Electron Device Letters</i> , 2022, 43, 541-544.	3.9	11
82	Mutually beneficial doping of tellurium and nitrogen in ZnO films grown by metal-organic chemical vapor deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2012, 30, .	2.1	10
83	Influence of oxygen precursors and annealing on Fe $_{3}\text{O}_4$ films grown on GaN templates by metal organic chemical vapor deposition. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014, 32, 052801.	1.2	10
84	Distinct enhancement of sub-bandgap photoresponse through intermediate band in high dose implanted ZnTe:O alloys. <i>Scientific Reports</i> , 2017, 7, 44399.	3.3	10
85	Photo-assisted hysteresis of electronic transport for ZnO nanowire transistors. <i>Nanotechnology</i> , 2018, 29, 115204.	2.6	10
86	Field-Plated NiO/Ga $_{2}\text{O}_3$ p-n Heterojunction Power Diodes With High-Temperature Thermal Stability and Near Unity Ideality Factors. <i>IEEE Journal of the Electron Devices Society</i> , 2021, 9, 1166-1171.	2.1	10
87	Raman probing of competitive laser heating and local recrystallization effect in ZnO nanocrystals. <i>Optics Express</i> , 2012, 20, 23281.	3.4	9
88	Temperature-dependent exciton-related transition energies mediated by carrier concentrations in unintentionally Al-doped ZnO films. <i>Applied Physics Letters</i> , 2013, 102, 221905.	3.3	9
89	The Luminescent Inhomogeneity and the Distribution of Zinc Vacancy-Related Acceptor-Like Defects in N-Doped ZnO Microrods. <i>Nanoscale Research Letters</i> , 2016, 11, 511.	5.7	9
90	Gate-first process compatible, high-quality <i>in situ</i> SiN $_{x}$ for surface passivation and gate dielectrics in AlGaIn/GaN MISHEMTs. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 305105.	2.8	9

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91	Large bandgap tunability of GaN/ZnO pseudobinary alloys through combined engineering of anions and cations. Applied Physics Letters, 2019, 115, .	3.3	9
92	Polarization-independent Indium Phosphide Nanowire Photodetectors. Advanced Optical Materials, 2020, 8, 2000514.	7.3	9
93	NiO/AlGaIn interface reconstruction and transport manipulation of p-NiO gated AlGaIn/GaN HEMTs. Applied Physics Reviews, 2021, 8, .	11.3	9
94	Over 1200 V Normally-OFF p-NiO Gated AlGaIn/GaN HEMTs on Si With a Small Threshold Voltage Shift. IEEE Electron Device Letters, 2022, 43, 268-271.	3.9	9
95	Optical fingerprints of donors and acceptors in high-quality NH ₃ -doped ZnO films. Optical Materials Express, 2017, 7, 1169.	3.0	8
96	Tailored Emission Properties of ZnTe/ZnTe:O/ZnO Core-Shell Nanowires Coupled with an Al Plasmonic Bowtie Antenna Array. ACS Nano, 2018, 12, 7327-7334.	14.6	8
97	1.26 W/mm Output Power Density at 10 GHz for Si ₃ N ₄ Passivated H-Terminated Diamond MOSFETs. IEEE Transactions on Electron Devices, 2021, 68, 5068-5072.	3.0	8
98	Unlocking the Single-Domain Heteroepitaxy of Orthorhombic $\text{In}_2\text{Ga}_2\text{O}_3$ via Phase Engineering. ACS Applied Electronic Materials, 2022, 4, 461-468.	4.3	8
99	Band alignment and polarization engineering in $\text{In}_2\text{Ga}_2\text{O}_3/\text{GaN}$ ferroelectric heterojunction. Science China: Physics, Mechanics and Astronomy, 2022, 65, .	5.1	8
100	Gate-first AlGaIn/GaN HEMT technology for enhanced threshold voltage stability based on MOCVD-grown <i>in situ</i> SiN _x . Journal Physics D: Applied Physics, 2021, 54, 015105.	2.8	7
101	Solution for Mass Production of High-Throughput Digital Microfluidic Chip Based on a-Si TFT with In-Pixel Boost Circuit. Micromachines, 2021, 12, 1199.	2.9	7
102	Vertical Field-Plated NiO/Ga ₂ O ₃ Heterojunction Power Diodes. , 2021, , .		6
103	Photoconductive and photovoltaic metal-semiconductor-metal $\text{In}_2\text{Ga}_2\text{O}_3$ solar-blind detectors with high rejection ratios. Journal Physics D: Applied Physics, 2022, 55, 394003.	2.8	6
104	The study of electronic structure and absorption coefficient of ZnTe:O alloys: A GGA+U method. Computational Materials Science, 2015, 109, 225-230.	3.0	5
105	Tailoring of nitrogen-vacancy colour centers in diamond epilayers by <i>in situ</i> sulfur and nitrogen anion engineering. Journal Physics D: Applied Physics, 2020, 53, 075107.	2.8	5
106	Property manipulation through pulsed laser annealing in high dose Mg-implanted GaN. Journal of Applied Physics, 2020, 128, .	2.5	5
107	Dislocation dynamics in <i>in situ</i> $\text{In}_2\text{Ga}_2\text{O}_3$ micropillars from selective-area epitaxy to epitaxial lateral overgrowth. Applied Physics Letters, 2022, 120, .	3.3	5
108	Comparative study of the effect of H ₂ addition on ZnO films grown by different zinc and oxygen precursors. Journal of Materials Research, 2015, 30, 935-945.	2.6	4

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109	Identification and tuning of zinc-site nitrogen-related complexes in ZnO material. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	4
110	Toward facile broadband photodetectors based on self-assembled ZnO nanobridge/rubrene heterointerface. Nanotechnology, 2019, 30, 065202.	2.6	4
111	Misfit epitaxial strain manipulated transport properties in cubic In ₂ O ₃ hetero-epilayers. Applied Physics Letters, 2020, 117, 102104.	3.3	4
112	Gate-Controlled NiO/Graphene/4H-SiC Double Schottky Barrier Heterojunction Based on a Metal-Oxide-Semiconductor Structure for Dual-Mode and Wide Range Ultraviolet Detection. ACS Applied Electronic Materials, 0, , .	4.3	4
113	Effect of the V/III ratio during buffer layer growth on the yellow and blue luminescence in undoped GaN epilayer. Science China: Physics, Mechanics and Astronomy, 2013, 56, 1694-1698.	5.1	3
114	Origin and transport properties of two-dimensional electron gas at ZnMgO/ZnO interface grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1268-1271.	0.8	3
115	Low-threshold ultraviolet stimulated emissions from large-sized single crystalline ZnO transferable membranes. Optics Express, 2018, 26, 31965.	3.4	3
116	First Demonstration of RESURF and Superjunction $\text{AlGaInGa}_{2/3}\text{O}_3$ MOSFETs with p-NiO/n- $\text{Ga}_{2/3}\text{O}_3$ Junctions. , 2021, , .		3
117	Strain-driven phase manipulation of $\text{In}_{1-x}\text{Ga}_x\text{N}$ and $\text{In}_{1-x}\text{Ga}_x\text{N}$ -Ga ₂ O ₃ by nanoepitaxial lateral overgrowth on embedded $\text{In}_{1-x}\text{Ga}_x\text{N}$ -In ₂ O ₃ submicron dots. Applied Physics Letters, 2021, 119, .	3.3	2
118	Numerical and experimental comparative study of metal-organic chemical vapor deposition of ZnO. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2007, 25, 187-190.	2.1	1
119	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. , 0, .		1
120	Chiral Metamaterials: A Terahertz Controlled NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials (Advanced Optical Materials 18/2017). Advanced Optical Materials, 2017, 5, .	7.3	0